Integrated Relay, Inductive Load Driver

This device is used to switch inductive loads such as relays, solenoids incandescent lamps, and small DC motors without the need of a free-wheeling diode. The device integrates all necessary items such as the MOSFET switch, ESD protection, and Zener clamps. It accepts logic level inputs thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

Features

- Provides a Robust Driver Interface Between D.C. Relay Coil and Sensitive Logic Circuits
- Optimized to Switch Relays from 3.0 V to 5.0 V Rail
- Capable of Driving Relay Coils Rated up to 2.5 W at 5.0 V
- Internal Zener Eliminates the Need of Free-Wheeling Diode
- Internal Zener Clamp Routes Induced Current to Ground for Quieter Systems Operation
- Low V_{DS(on)} Reduces System Current Drain
- Pb–Free Package is Available

Typical Applications

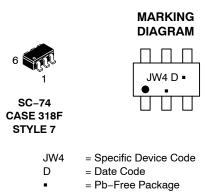
- Telecom: Line Cards, Modems, Answering Machines, FAX
- Computers and Office: Photocopiers, Printers, Desktop Computers
- Consumer: TVs and VCRs, Stereo Receivers, CD Players, Cassette Recorders
- Industrial: Small Appliances, Security Systems, Automated Test Equipment, Garage Door Openers
- Automotive: 5.0 V Driven Relays, Motor Controls, Power Latches, Lamp Drivers



ON Semiconductor®

http://onsemi.com

Relay, Inductive Load Driver 0.5 Amp, 8.0 V Clamp

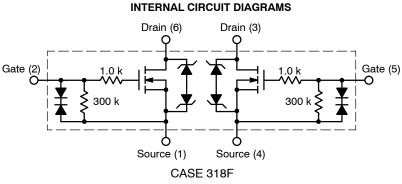


(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NUD3105DMT1	SC-74	3000/Tape & Reel
NUD3105DMT1G	SC-74 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



MAXIMUM RATINGS (T_J = 25° C unless otherwise specified)

Symbol	Rating	Value	Unit
V _{DSS}	Drain to Source Voltage – Continuous	6.0	V _{dc}
V _{GS}	Gate to Source Voltage – Continuous	6.0	V _{dc}
I _D	Drain Current – Continuous	500	mA
Ez	Single Pulse Drain-to-Source Avalanche Energy (T _{Jinitial =} 25°C)	50	mJ
TJ	Junction Temperature	150	°C
T _A	Operating Ambient Temperature	-40 to 85	°C
T _{stg}	Storage Temperature Range	−65 to +150	°C
PD	Total Power Dissipation (Note 1) Derating Above 25°C		mW mW/°C
R_{\thetaJA}	Thermal Resistance Junction-to-Ambient	329	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 This device contains ESD protection and exceeds the following tests: Human Body Model 2000 V per MIL_STD-883, Method 3015. Machine Model Method 200 V.

TYPICAL ELECTRICAL CHARACTERISTICS (T_J = $25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic	Min	Тур	Max	Unit
OFF CHAR	ACTERISTICS	•			-
V _{BRDSS}	Drain to Source Sustaining Voltage (Internally Clamped) (I _D = 10 mA)	6.0	8.0	9.0	V
B _{VGSO}	l _g = 1.0 mA	-	-	8.0	V
I _{DSS}	Drain to Source Leakage Current $(V_{DS} = 5.5 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C})$ $(V_{DS} = 5.5 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 85^{\circ}\text{C})$			15 15	μΑ
I _{GSS}	$ \begin{array}{l} \mbox{Gate Body Leakage Current} \\ (V_{GS}=3.0 \ \mbox{V}, \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	5.0		35 65	μΑ
ON CHARA	CTERISTICS	•			-
$V_{GS(th)}$	Gate Threshold Voltage $ \begin{pmatrix} V_{GS} = V_{DS}, \ I_D = 1.0 \text{ mA} \end{pmatrix} \\ (V_{GS} = V_{DS}, \ I_D = 1.0 \text{ mA}, \ T_J = 85^\circ\text{C}) $	0.8 0.8	1.2 -	1.4 1.4	v
R _{DS(on)}	$ Drain to Source On-Resistance \\ (I_D = 250 \text{ mA}, \text{V}_{GS} = 3.0 \text{ V}) \\ (I_D = 500 \text{ mA}, \text{V}_{GS} = 3.0 \text{ V}) \\ (I_D = 500 \text{ mA}, \text{V}_{GS} = 5.0 \text{ V}) \\ (I_D = 500 \text{ mA}, \text{V}_{GS} = 3.0 \text{ V}, \text{T}_J = 85^{\circ}\text{C}) \\ (I_D = 500 \text{ mA}, \text{V}_{GS} = 5.0 \text{ V}, \text{T}_J = 85^{\circ}\text{C}) $	- - - -	- - - - -	1.2 1.3 0.9 1.3 0.9	Ω
I _{DS(on)}	Output Continuous Current ($V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V}$) ($V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V}, T_J = 85^{\circ}\text{C}$)	300 200	400 _	-	mA
g fs	Forward Transconductance (V _{OUT} = 5.0 V, I _{OUT} = 0.25 A)	350	570	-	mMhos

TYPICAL ELECTRICAL CHARACTERISTICS (T_J = $25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic		Тур	Max	Unit
DYNAMIC C	HARACTERISTICS				
C _{iss}	Input Capacitance $(V_{DS} = 5.0 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 10 \text{ kHz})$	-	25	-	pF
C _{oss}	Output Capacitance (V _{DS} = 5.0 V, V _{GS} = 0 V, f = 10 kHz)	_	37	-	pF
C _{rss}	Transfer Capacitance (V _{DS} = 5.0 V, V _{GS} = 0 V, f = 10 kHz)	-	8.0	-	pF

SWITCHING CHARACTERISTICS

Symbol	Characteristic	Min	Тур	Max	Units
	Propagation Delay Times:				nS
t _{PHL}	High to Low Propagation Delay; Figure 1 (5.0 V)	_	25	-	
t _{PLH}	Low to High Propagation Delay; Figure 1 (5.0 V)	-	80	-	
t _{PHL}	High to Low Propagation Delay; Figure 1 (3.0 V)	-	44	_	
t _{PLH}	Low to High Propagation Delay; Figure 1 (3.0 V)	-	44	-	
	Transition Times:				nS
t _f	Fall Time; Figure 1 (5.0 V)	_	23	-	
t _r	Rise Time; Figure 1 (5.0 V)	-	32	-	
t _f	Fall Time; Figure 1 (3.0 V)	_	53	_	
t _r	Rise Time; Figure 1 (3.0 V)	-	30	-	-

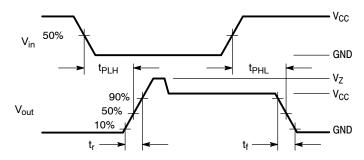


Figure 1. Switching Waveforms

TYPICAL CHARACTERISTICS

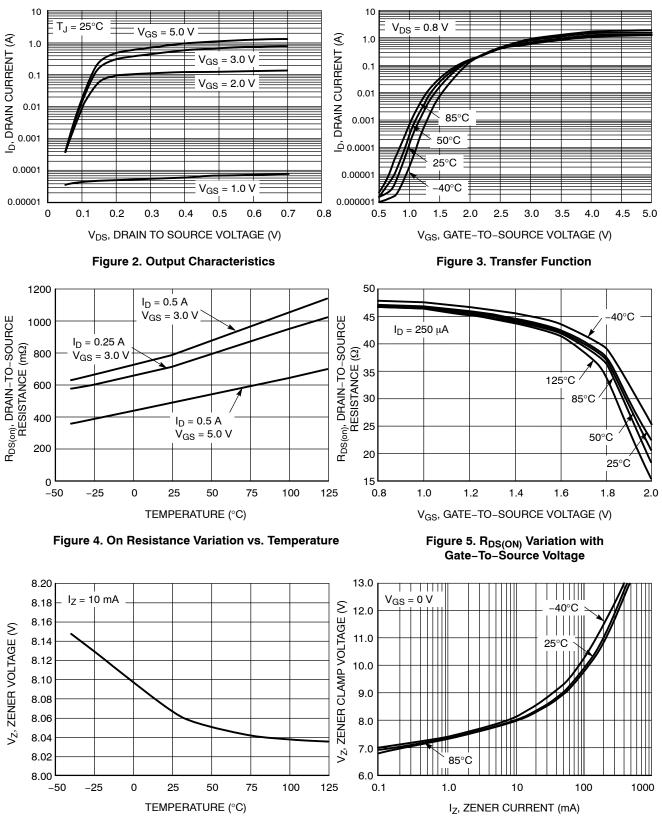
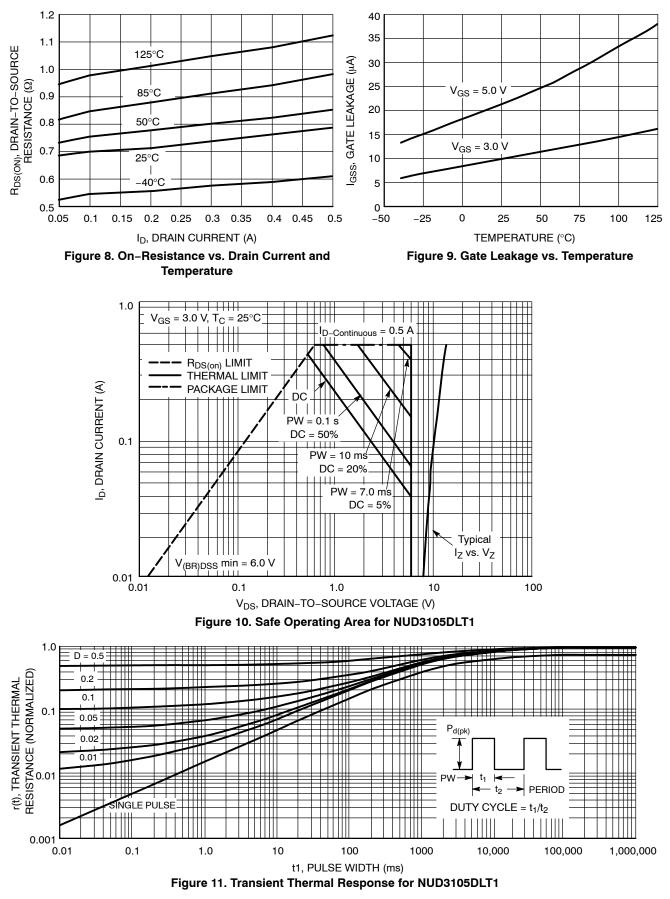


Figure 6. Zener Voltage vs. Temperature

Figure 7. Zener Clamp Voltage vs. Zener Current

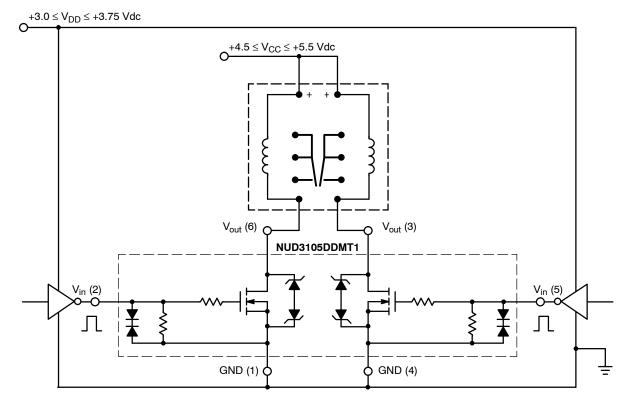




Designing with this Data Sheet

- 1. Determine the maximum inductive load current (at max V_{CC} , min coil resistance & usually minimum temperature) that the NUD3105D will have to drive and make sure it is less than the max rated current.
- 2. For pulsed operation, use the Transient Thermal Response of Figure 11 and the instructions with it to determine the maximum limit on transistor power dissipation for the desired duty cycle and temperature range.
- 3. Use Figures 10 and 11 with the SOA notes to insure that instantaneous operation does not push the device beyond the limits of the SOA plot.

- 4. Verify that the circuit driving the gate will meet the $V_{GS(th)}$ from the Electrical Characteristics table.
- 5. Using the max output current calculated in step 1, check Figure 7 to insure that the range of Zener clamp voltage over temperature will satisfy all system & EMI requirements.
- 6. Use I_{GSS} and I_{DSS} from the Electrical Characteristics table to insure that "OFF" state leakage over temperature and voltage extremes does not violate any system requirements.
- 7. Review circuit operation and insure none of the device max ratings are being exceeded.



APPLICATIONS DIAGRAMS

Figure 12. A 200 mW, 5.0 V Dual Coil Latching Relay Application with 3.0 V Level Translating Interface

Max Continuous Current Calculation

 $\begin{array}{l} \mbox{for TX2-5V Relay, R1 = 178 } \Omega \ \mbox{Nominal @ R_A = 25°C} \\ \mbox{Assuming } \pm 10\% \ \mbox{Make Tolerance,} \\ \mbox{R1 = 178 } \Omega \ ^* \ 0.9 = 160 \ \Omega \ \mbox{Min @ T_A = 25°C} \\ \mbox{T_C for Annealed Copper Wire is } 0.4\%/^{\circ}C \\ \mbox{R1 = 160 } \Omega \ ^* \ \mbox{[1+(0.004) * (-40^{\circ}-25^{\circ})] = 118 } \Omega \ \mbox{Min @ -40^{\circ}C} \\ \mbox{I_O Max = (5.5 V Max - 0.25V) / 118 } \Omega = 45 \ \mbox{mA} \\ \end{array}$

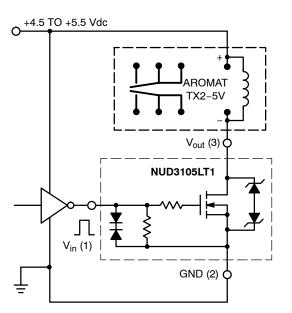


Figure 13. A 140 mW, 5.0 V Relay with TTL Interface

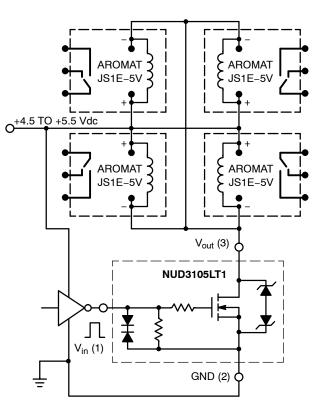
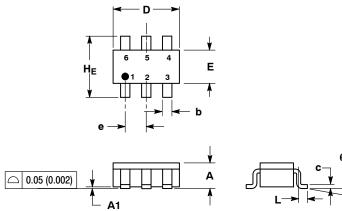


Figure 14. A Quad 5.0 V, 360 mW Coil Relay Bank

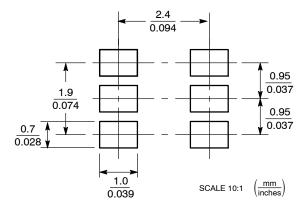




SCALE 2:1



SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DATE 08 JUN 2012	2

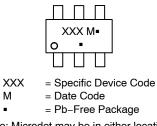
NOTES:

SC-74 CASE 318F-05 **ISSUE N**

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- CONTROLING DIMENSION: INCH. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM З.
- THICKNESS OF BASE MATERIAL. 4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
С	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
Е	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

GENERIC **MARKING DIAGRAM***



(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. CATHODE	PIN 1. NO CONNECTION	PIN 1. EMITTER 1	PIN 1. COLLECTOR 2	PIN 1. CHANNEL 1	PIN 1. CATHODE
2. ANODE	2. COLLECTOR	2. BASE 1	2. EMITTER 1/EMITTER 2	2. ANODE	2. ANODE
3. CATHODE	3. EMITTER	3. COLLECTOR 2	3. COLLECTOR 1	3. CHANNEL 2	3. CATHODE
4. CATHODE	4. NO CONNECTION	4. EMITTER 2	4. EMITTER 3	4. CHANNEL 3	4. CATHODE
5. ANODE	5. COLLECTOR	5. BASE 2	5. BASE 1/BASE 2/COLLECTOR 3	5. CATHODE	5. CATHODE
6. CATHODE	6. BASE	6. COLLECTOR 1	6. BASE 3	6. CHANNEL 4	6. CATHODE
STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:	E
PIN 1. SOURCE 1	PIN 1. EMITTER 1	PIN 1. EMITTER 2	PIN 1. ANODE/CATHODE	PIN 1. EMITTER	
2. GATE 1	2. BASE 2	2. BASE 2	2. BASE	2. BASE	
3. DRAIN 2	3. COLLECTOR 2	3. COLLECTOR 1	3. EMITTER	3. ANODE/CATHOD	
4. SOURCE 2	4. EMITTER 2	4. EMITTER 1	4. COLLECTOR	4. ANODE	
5. GATE 2	5. BASE 1	5. BASE 1	5. ANODE	5. CATHODE	
6. DRAIN 1	6. COLLECTOR 1	6. COLLECTOR 2	6. CATHODE	6. COLLECTOR	

DOCUMENT NUMBER:	98ASB42973B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SC-74	PAGE 1 OI			

ON Semiconductor and ()) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights or the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

Email Requests to: orderlit@onsemi.com onsemi Website: www.onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

NUD3105DMT1 NUD3105DMT1G SZNUD3105DMT1G